# **VP2106**

# P-Channel Enhancement-Mode Vertical DMOS FET

#### **Features**

- · Free from Secondary Breakdown
- · Low Power Drive Requirement
- · Ease of Paralleling
- Low C<sub>ISS</sub> and Fast Switching Speeds
- · Excellent Thermal Stability
- · Integral Source-Drain Diode
- · High Input Impedance and High Gain

### **Applications**

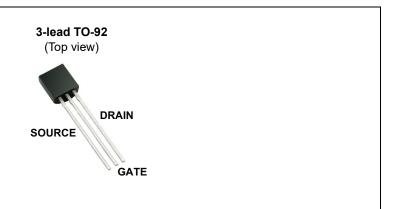
- · Motor Controls
- · Converters
- Amplifiers
- · Switches
- · Power Supply Circuits
- Drivers (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

### **General Description**

The VP2106 Enhancement-mode (normally-off) transistors use a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited for a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

### **Package Type**



See Table 3-1 for pin information.

### 1.0 ELECTRICAL CHARACTERISTICS

### **Absolute Maximum Ratings†**

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	500
Gate-to-Source Voltage	200
Operating Ambient Temperature, T <sub>A</sub>	
Storage Temperature, T <sub>S</sub>	

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:**  $T_A$  = 25°C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300  $\mu$ s pulse, 2% duty cycle

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$V_{GS} = 0V$ , $I_D = -1$ mA
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.5	_	-3.5	V	$V_{GS} = V_{DS}$ , $I_D = -1$ mA
Change in V <sub>GS(th)</sub> with Temperature	$\Delta V_{GS(th)}$		5.8	6.5	mV/°C	$V_{GS} = V_{DS}$ , $I_D = -1$ mA (Note 1)
Gate Body Leakage Current	I <sub>GSS</sub>	_	-1	-100	nA	$V_{GS}$ = ±20V, $V_{DS}$ = 0V
	I <sub>DSS</sub>	_	_	-10	μΑ	V <sub>GS</sub> = 0V, V <sub>DS</sub> = Maximum rating
Zero-Gate Voltage Drain Current				-1	mA	$V_{DS}$ = 0.8 Maximum rating, $V_{GS}$ = 0V, $T_A$ = 125°C (Note 1)
On-State Drain Current	I <sub>D(ON)</sub>	-0.5	-1	_	Α	$V_{GS} = -10V, V_{DS} = -25V$
Static Drain-to-Source On-State Resistance	D	l	11	15	Ω	$V_{GS} = -5V$ , $I_{D} = -100 \text{ mA}$
Static Diani-to-Source On-State Resistance	R <sub>DS(ON)</sub>		9	12	Ω	$V_{GS} = -10V$ , $I_{D} = -500$ mA
Change in R <sub>DS(ON)</sub> with Temperature	$\Delta R_{DS(ON)}$	_	0.55	1	%/°C	$V_{GS} = -10V$ , $I_{D} = -500 \text{ mA}$ (Note 1)

Note 1: Specification is obtained by characterization and is not 100% tested.

### **AC ELECTRICAL CHARACTERISTICS**

<b>Electrical Specifications:</b> T <sub>A</sub> = 25°C unless otherwise specified. All AC parameters are not 100% sample tested.										
Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions				
Forward Transconductance	G <sub>FS</sub>	150	200	_	mmho	$V_{DS} = -25V$ , $I_{D} = -500$ mA				
Input Capacitance	C <sub>ISS</sub>	_	45	60	pF	$V_{GS} = 0V$ ,				
Common-Source Output Capacitance	Coss	_	22	30		$V_{DS} = -25V$ ,				
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	3	8	pF	f = 1 MHz				
Turn-On Delay Time	t <sub>d(ON)</sub>	_	4	5	ns					
Rise Time	t <sub>r</sub>	_	5	8	ns	$V_{DD} = -25V,$				
Turn-Off Delay Time	t <sub>d(OFF)</sub>	_	5	9	ns	$I_D = -500 \text{ mA},$ $R_{GEN} = 25\Omega$				
Fall Time	t <sub>f</sub>	_	4	8	ns	-GEN				
DIODE PARAMETER										
Diode Forward Voltage Drop	V <sub>SD</sub>	_	-1.2	-2	V	$V_{GS} = 0V$ , $I_{SD} = -500$ mA ( <b>Note 1</b> )				
Reverse Recovery Time	t <sub>rr</sub>	_	400	_	ns	$V_{GS} = 0V$ , $I_{SD} = -500 \text{ mA}$				

**Note 1:** Unless otherwise stated, all DC parameters are 100% tested at 25°C. Pulse test: 300 μs pulse, 2% duty cycle

### **TEMPERATURE SPECIFICATIONS**

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions
TEMPERATURE RANGE						
Operating Ambient Temperature	T <sub>A</sub>	-55	_	+150	°C	
Storage Temperature		-55	_	+150	°C	
PACKAGE THERMAL RESISTANCE						
3-lead TO-92	$\theta_{JA}$	_	132	_	°C/W	

### THERMAL CHARACTERISTICS

Package	I <sub>D</sub> (Note 1) (Continuous) (mA)	I <sub>D</sub> (Pulsed) (mA)	Power Dissipation at T <sub>A</sub> = 25°C (W)	I <sub>DR</sub> (Note 1) (mA)	I <sub>DRM</sub> (mA)
3-lead TO-92	-250	-800	1	-250	-800

Note 1:  $I_D$  (continuous) is limited by maximum rated  $T_J$ .

Note:

### 2.0 TYPICAL PERFORMANCE CURVES

The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

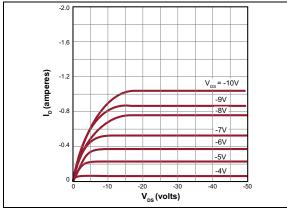


FIGURE 2-1: Output Characteristics.

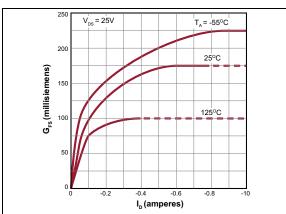
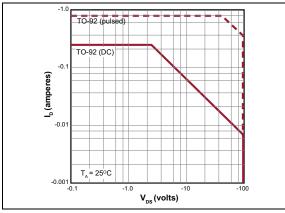


FIGURE 2-2: Transconductance vs. Drain Current.



**FIGURE 2-3:** Maximum Rated Safe Operating Area.

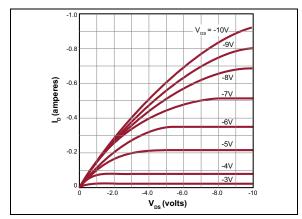
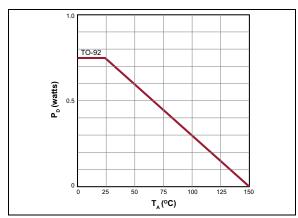
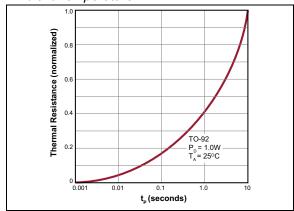


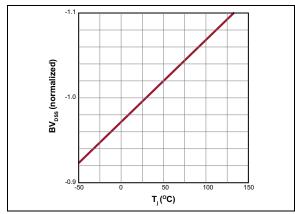
FIGURE 2-4: Saturation Characteristics.



**FIGURE 2-5:** Power Dissipation vs. Ambient Temperature.



**FIGURE 2-6:** Thermal Response Characteristics.



**FIGURE 2-7:**  $BV_{DSS}$  Variation with Temperature.

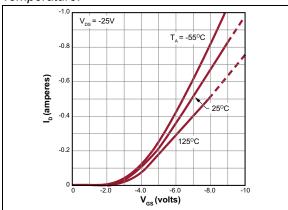
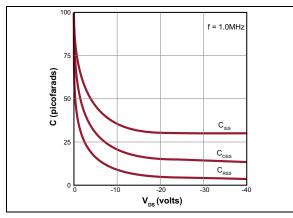


FIGURE 2-8: Transfer Characteristics.



**FIGURE 2-9:** Capacitance vs. Drain-to-Source Voltage.

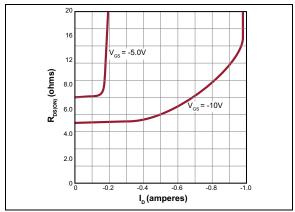
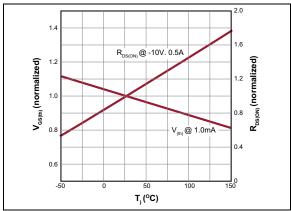


FIGURE 2-10: On-Resistance vs. Drain Current.



**FIGURE 2-11:**  $V_{(th)}$  and  $R_{DS}$  Variation with Temperature.

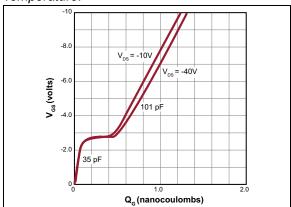


FIGURE 2-12: Gate Drive Dynamic Characteristics.

### 3.0 PIN DESCRIPTION

The details on the pins of VP2106 are listed in Table 3-1. Refer to **Package Type** for the location of pins.

TABLE 3-1: 3-LEAD TO-92 PIN FUNCTION TABLE

Pin Number	Pin Name	Description						
1	Source	Source						
2	Gate	Gate						
3	Drain	Drain						

### 4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for VP2106.

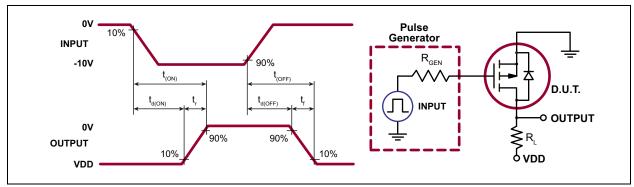


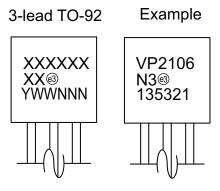
FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

Device	BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	R <sub>DS(ON)</sub> (Maximum) (Ω)	I <sub>D(ON)</sub> (Minimum) (mA)
VP2106	-60	12	-500

#### 5.0 PACKAGING INFORMATION

#### 5.1 **Package Marking Information**



Legend: XX...X Product Code or Customer-specific information

Year code (last digit of calendar year) YY Year code (last 2 digits of calendar year) WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

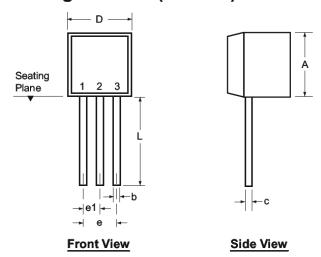
Pb-free JEDEC® designator for Matte Tin (Sn) (e3)

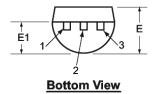
This package is Pb-free. The Pb-free JEDEC designator (@3)

can be found on the outer packaging for this package.

In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

## 3-Lead TO-92 Package Outline (L/LL/N3)





Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symb	ool	Α	b	С	D	E	E1	е	e1	L
	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
Dimensions (inches)	NOM	-	-	-	-	-	-	-	-	-
(51100)	MAX	.210	.022 <sup>†</sup>	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
\* This dimension is not specified in the JEDEC drawing.
† This dimension differs from the JEDEC drawing.

Drawings not to scale.



NOTES:

### **APPENDIX A: REVISION HISTORY**

### **Revision A (December 2021)**

- Converted Supertex Doc# DSFP-VP2106 to Microchip DS20006007A
- Changed the package marking format
- Removed the 3-Lead TO-92 N3 P002, P003, P005, P013, and P014 media types to align packaging specifications with the actual BQM
- Added sections to comply with Microchip formatting standards
- Made minor text changes throughout the document

### PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

<u> </u>		- <u>x</u> - <u>x</u>	Example:			
Package Options				Environmental Media Type	a) VP2106N3-G:	P-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92, 1000/Bag
VP2106	=	P-Channel Enhancement-Mode Vertical DMOS FET				
N3	=	3-lead TO-92				
G	=	Lead (Pb)-free/RoHS-compliant Package				
(blank)	=	1000/Bag for an N3 Package				
	Packa Option VP2106 N3	Package Options  VP2106 =  N3 =  G =	Package Options  Environmental Media Type  VP2106 = P-Channel Enhancement-Mode Vertical DMOS FET  N3 = 3-lead TO-92  G = Lead (Pb)-free/RoHS-compliant Package	Package Options  Environmental Media Type  a) VP2106N3-G:  VP2106 = P-Channel Enhancement-Mode Vertical DMOS FET  N3 = 3-lead TO-92  G = Lead (Pb)-free/RoHS-compliant Package		

#### Note the following details of the code protection feature on Microchip products:

- Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner, within operating specifications, and under normal conditions
- Microchip values and aggressively protects its intellectual property rights. Attempts to breach the code protection features of Microchip product is strictly prohibited and may violate the Digital Millennium Copyright Act.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code protection does not
  mean that we are guaranteeing the product is "unbreakable". Code protection is constantly evolving. Microchip is committed to
  continuously improving the code protection features of our products.

This publication and the information herein may be used only with Microchip products, including to design, test, and integrate Microchip products with your application. Use of this information in any other manner violates these terms. Information regarding device applications is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. Contact your local Microchip sales office for additional support or, obtain additional support at <a href="https://www.microchip.com/en-us/support/design-help/client-support-services">https://www.microchip.com/en-us/support/design-help/client-support-services</a>.

THIS INFORMATION IS PROVIDED BY MICROCHIP "AS IS". MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION INCLUDING BUT NOT LIMITED TO ANY IMPLIED WARRANTIES OF NON-INFRINGEMENT, MERCHANTABILITY, AND FITNESS FOR A PARTICULAR PURPOSE, OR WARRANTIES RELATED TO ITS CONDITION, QUALITY, OR PERFORMANCE.

IN NO EVENT WILL MICROCHIP BE LIABLE FOR ANY INDIRECT, SPECIAL, PUNITIVE, INCIDENTAL, OR CONSEQUENTIAL LOSS, DAMAGE, COST, OR EXPENSE OF ANY KIND WHATSOEVER RELATED TO THE INFORMATION OR ITS USE, HOWEVER CAUSED, EVEN IF MICROCHIP HAS BEEN ADVISED OF THE POSSIBILITY OR THE DAMAGES ARE FORESEEABLE. TO THE FULLEST EXTENT ALLOWED BY LAW, MICROCHIP'S TOTAL LIABILITY ON ALL CLAIMS IN ANY WAY RELATED TO THE INFORMATION OR ITS USE WILL NOT EXCEED THE AMOUNT OF FEES, IF ANY, THAT YOU HAVE PAID DIRECTLY TO MICROCHIP FOR THE INFORMATION.

Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.

#### **Trademarks**

The Microchip name and logo, the Microchip logo, Adaptec, AnyRate, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, CryptoMemory, CryptoRF, dsPIC, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AgileSwitch, APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, Flashtec, Hyper Speed Control, HyperLight Load, IntelliMOS, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet-Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, TrueTime, WinPath, and ZL are registered trademarks of Microchip Technology Incorporated in the ILS A

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, AnyIn, AnyOut, Augmented Switching, BlueSky, BodyCom, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, Espresso T1S, EtherGREEN, GridTime, IdealBridge, In-Circuit Serial Programming, ICSP, INICnet, Intelligent Paralleling, Inter-Chip Connectivity, JitterBlocker, Knob-on-Display, maxCrypto, maxView, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, NVM Express, NVMe, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, RTAX, RTG4, SAM-ICE, Serial Quad I/O, simpleMAP, SimpliPHY, SmartBuffer, SmartHLS, SMART-I.S., storClad, SQI, SuperSwitcher, SuperSwitcher II, Switchtec, SynchroPHY, Total Endurance, TSHARC, USBCheck, VariSense, VectorBlox, VeriPHY, ViewSpan, WiperLock, XpressConnect, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

 $\ensuremath{\mathsf{SQTP}}$  is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, Symmcom, and Trusted Time are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2021, Microchip Technology Incorporated and its subsidiaries.

All Rights Reserved.

ISBN: 978-1-5224-9516-1



### Worldwide Sales and Service

#### **AMERICAS**

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200

Tel: 480-792-7200 Fax: 480-792-7277 Technical Support:

http://www.microchip.com/ support

Web Address:

www.microchip.com

**Atlanta** Duluth, GA

Tel: 678-957-9614 Fax: 678-957-1455

**Austin, TX** Tel: 512-257-3370

**Boston** 

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

**Detroit** Novi, MI

Tel: 248-848-4000

Houston, TX

Tel: 281-894-5983 Indianapolis

Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453 Tel: 317-536-2380

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608 Tel: 951-273-7800

**Raleigh, NC** Tel: 919-844-7510

New York, NY Tel: 631-435-6000

San Jose, CA Tel: 408-735-9110

Tel: 408-436-4270

Canada - Toronto
Tel: 905-695-1980
Fax: 905-695-2078

#### ASIA/PACIFIC

Australia - Sydney Tel: 61-2-9868-6733

**China - Beijing** Tel: 86-10-8569-7000

China - Chengdu Tel: 86-28-8665-5511

China - Chongqing Tel: 86-23-8980-9588

**China - Dongguan** Tel: 86-769-8702-9880

China - Guangzhou Tel: 86-20-8755-8029

China - Hangzhou Tel: 86-571-8792-8115

China - Hong Kong SAR Tel: 852-2943-5100

**China - Nanjing** Tel: 86-25-8473-2460

China - Qingdao Tel: 86-532-8502-7355

**China - Shanghai** Tel: 86-21-3326-8000

China - Shenyang

Tel: 86-24-2334-2829 China - Shenzhen

Tel: 86-755-8864-2200

**China - Suzhou** Tel: 86-186-6233-1526

**China - Wuhan** Tel: 86-27-5980-5300

**China - Xian** Tel: 86-29-8833-7252

China - Xiamen
Tel: 86-592-2388138

**China - Zhuhai** Tel: 86-756-3210040

#### ASIA/PACIFIC

India - Bangalore Tel: 91-80-3090-4444

India - New Delhi Tel: 91-11-4160-8631

India - Pune Tel: 91-20-4121-0141

**Japan - Osaka** Tel: 81-6-6152-7160

Japan - Tokyo

Tel: 81-3-6880- 3770 Korea - Daegu

Tel: 82-53-744-4301

Korea - Seoul Tel: 82-2-554-7200

Malaysia - Kuala Lumpur Tel: 60-3-7651-7906

Malaysia - Penang Tel: 60-4-227-8870

Philippines - Manila Tel: 63-2-634-9065

**Singapore** Tel: 65-6334-8870

**Taiwan - Hsin Chu** Tel: 886-3-577-8366

Taiwan - Kaohsiung Tel: 886-7-213-7830

**Taiwan - Taipei** Tel: 886-2-2508-8600

Thailand - Bangkok Tel: 66-2-694-1351

Vietnam - Ho Chi Minh Tel: 84-28-5448-2100

#### **EUROPE**

**Austria - Wels** Tel: 43-7242-2244-39 Fax: 43-7242-2244-393

Denmark - Copenhagen Tel: 45-4485-5910

Fax: 45-4485-2829

Finland - Espoo Tel: 358-9-4520-820

France - Paris
Tel: 33-1-69-53-63-20
Fax: 33-1-69-30-90-79

Germany - Garching Tel: 49-8931-9700

**Germany - Haan** Tel: 49-2129-3766400

Germany - Heilbronn Tel: 49-7131-72400

**Germany - Karlsruhe** Tel: 49-721-625370

**Germany - Munich** Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Germany - Rosenheim Tel: 49-8031-354-560

Israel - Ra'anana Tel: 972-9-744-7705

**Italy - Milan** Tel: 39-0331-742611

Fax: 39-0331-466781 **Italy - Padova** Tel: 39-049-7625286

**Netherlands - Drunen** Tel: 31-416-690399 Fax: 31-416-690340

Norway - Trondheim Tel: 47-7288-4388

**Poland - Warsaw** Tel: 48-22-3325737

Romania - Bucharest Tel: 40-21-407-87-50

**Spain - Madrid** Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

**Sweden - Gothenberg** Tel: 46-31-704-60-40

Sweden - Stockholm Tel: 46-8-5090-4654

**UK - Wokingham** Tel: 44-118-921-5800 Fax: 44-118-921-5820

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

### Microchip:

<u>VP2106N3-P014-G</u> <u>VP2106N3-P002-G</u> <u>VP2106N3-P002</u> <u>VP2106N3-P014</u> <u>VP2106N3-P013</u> <u>VP2106N3-P013</u> <u>VP2106N3-P003</u> <u>VP2106N3-P013-G</u> <u>VP2106N3-P003-G</u> <u>VP2106N3-G</u> <u>VP2106N3-G</u> <u>VP2106N3-G P013</u> <u>VP2106N3-G P002</u> <u>VP2106N3-G P005</u> <u>VP2106N3-G P003</u> <u>VP2106N3-G P014</u>